

Qian Sun ǎ-é'±

List of Publications by Year in descending order

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141
papers

3,578
citations

126708

33
h-index

168136

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142
all docs

142
docs citations

142
times ranked

3109
citing authors

#	ARTICLE	IF	CITATIONS
1	Room-temperature continuous-wave electrically injected InGaN-based laser directly grown on Si. <i>Nature Photonics</i> , 2016, 10, 595-599.	15.6	191
2	One-step hydrothermal process to prepare highly crystalline Fe ₃ O ₄ nanoparticles with improved magnetic properties. <i>Materials Research Bulletin</i> , 2003, 38, 1113-1118.	2.7	189
3	Room-temperature continuous-wave electrically pumped InGaN/GaN quantum well blue laser diode directly grown on Si. <i>Light: Science and Applications</i> , 2018, 7, 13.	7.7	101
4	Understanding nonpolar GaN growth through kinetic Wulff plots. <i>Journal of Applied Physics</i> , 2008, 104, .	1.1	98
5	Studies on High-Voltage GaN-on-Si MIS-HEMTs Using LPCVD Si ₃ N ₄ as Gate Dielectric and Passivation Layer. <i>IEEE Transactions on Electron Devices</i> , 2016, 63, 731-738.	1.6	96
6	Normally OFF GaN-on-Si MIS-HEMTs Fabricated With LPCVD-SiN _x Passivation and High-Temperature Gate Recess. <i>IEEE Transactions on Electron Devices</i> , 2016, 63, 614-619.	1.6	87
7	Ultrathin-Barrier AlGaN/GaN Heterostructure: A Recess-Free Technology for Manufacturing High-Performance GaN-on-Si Power Devices. <i>IEEE Transactions on Electron Devices</i> , 2018, 65, 207-214.	1.6	87
8	Understanding and controlling heteroepitaxy with the kinetic Wulff plot: A case study with GaN. <i>Journal of Applied Physics</i> , 2011, 110, .	1.1	85
9	A conductivity-based selective etching for next generation GaN devices. <i>Physica Status Solidi (B): Basic Research</i> , 2010, 247, 1713-1716.	0.7	84
10	Heteroepitaxy of AlGaN on bulk AlN substrates for deep ultraviolet light emitting diodes. <i>Applied Physics Letters</i> , 2007, 91, 051116.	1.5	79
11	Morphological and microstructural evolution in the two-step growth of nonpolar a-plane GaN on r-plane sapphire. <i>Journal of Applied Physics</i> , 2009, 106, .	1.1	74
12	Improving microstructural quality of semipolar (112̄±2) GaN on m-plane sapphire by a two-step growth process. <i>Applied Physics Letters</i> , 2009, 95, .	1.5	72
13	High Uniformity Normally-OFF GaN MIS-HEMTs Fabricated on Ultra-Thin-Barrier AlGaN/GaN Heterostructure. <i>IEEE Electron Device Letters</i> , 2016, 37, 1617-1620.	2.2	72
14	Nitrogen-polar GaN growth evolution on c-plane sapphire. <i>Applied Physics Letters</i> , 2008, 93, .	1.5	67
15	Using the kinetic Wulff plot to design and control nonpolar and semipolar GaN heteroepitaxy. <i>Semiconductor Science and Technology</i> , 2012, 27, 024005.	1.0	67
16	GaN-on-Si blue/white LEDs: epitaxy, chip, and package. <i>Journal of Semiconductors</i> , 2016, 37, 044006.	2.0	66
17	A wireless, implantable optoelectrochemical probe for optogenetic stimulation and dopamine detection. <i>Microsystems and Nanoengineering</i> , 2020, 6, 64.	3.4	57
18	The fabrication of large-area, free-standing GaN by a novel nanoetching process. <i>Nanotechnology</i> , 2011, 22, 045603.	1.3	56

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19	Strain relaxation and dislocation reduction in AlGaIn step-graded buffer for crack-free GaN on Si (111). <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2014, 11, 437-441.	0.8	56
20	Reduction of stacking fault density in m-plane GaN grown on SiC. <i>Applied Physics Letters</i> , 2008, 93, .	1.5	55
21	On-Chip Integration of GaN-Based Laser, Modulator, and Photodetector Grown on Si. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2018, 24, 1-5.	1.9	55
22	A review on the GaN-on-Si power electronic devices. <i>Fundamental Research</i> , 2022, 2, 462-475.	1.6	54
23	Influence of dislocations on photoluminescence of InGaIn-GaN multiple quantum wells. <i>Applied Physics Letters</i> , 2005, 87, 071908.	1.5	53
24	Improved hydrogen detection sensitivity in N-polar GaN Schottky diodes. <i>Applied Physics Letters</i> , 2009, 94, 212108.	1.5	51
25	N-face GaN growth on c-plane sapphire by metalorganic chemical vapor deposition. <i>Journal of Crystal Growth</i> , 2009, 311, 2948-2952.	0.7	51
26	Normally-off HEMTs With Regrown p-GaN Gate and Low-Pressure Chemical Vapor Deposition SiN _x Passivation by Using an AlN Pre-Layer. <i>IEEE Electron Device Letters</i> , 2019, 40, 1495-1498.	2.2	50
27	Mechanical Properties of Nanoporous GaN and Its Application for Separation and Transfer of GaN Thin Films. <i>ACS Applied Materials & Interfaces</i> , 2013, 5, 11074-11079.	4.0	45
28	On-wafer fabrication of cavity mirrors for InGaIn-based laser diode grown on Si. <i>Scientific Reports</i> , 2018, 8, 7922.	1.6	44
29	p-GaN Gate Enhancement-Mode HEMT Through a High Tolerance Self-Terminated Etching Process. <i>IEEE Journal of the Electron Devices Society</i> , 2017, 5, 340-346.	1.2	43
30	III-nitride semiconductor lasers grown on Si. <i>Progress in Quantum Electronics</i> , 2021, 77, 100323.	3.5	38
31	Effect of Controlled Growth Dynamics on the Microstructure of Nonpolar-a-Plane GaN Revealed by X-ray Diffraction. <i>Japanese Journal of Applied Physics</i> , 2009, 48, 071002.	0.8	37
32	Room-Temperature Electrically Injected AlGaIn-Based near-Ultraviolet Laser Grown on Si. <i>ACS Photonics</i> , 2018, 5, 699-704.	3.2	37
33	High-Voltage and High-I _{ON} /I _{OFF} Quasi-Vertical GaN-on-Si Schottky Barrier Diode With Argon-Implanted Termination. <i>IEEE Electron Device Letters</i> , 2021, 42, 473-476.	2.2	37
34	Transfer-printed, tandem microscale light-emitting diodes for full-color displays. <i>Proceedings of the National Academy of Sciences of the United States of America</i> , 2021, 118, .	3.3	33
35	Low-temperature growth of InN by MOCVD and its characterization. <i>Journal of Crystal Growth</i> , 2005, 276, 13-18.	0.7	32
36	Lateral phase separation in AlGaIn grown on GaN with a high-temperature AlN interlayer. <i>Applied Physics Letters</i> , 2005, 87, 121914.	1.5	32

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37	Role of nonradiative recombination centers and extended defects in nonpolar GaN on light emission efficiency. Applied Physics Letters, 2011, 98, .	1.5	32
38	Microstructural evolution in m-plane GaN growth on m-plane SiC. Applied Physics Letters, 2008, 92, 051112.	1.5	30
39	Self-terminated etching of GaN with a high selectivity over AlGaIn under inductively coupled Cl ₂ /N ₂ /O ₂ plasma with a low-energy ion bombardment. Applied Surface Science, 2017, 420, 817-824.	3.1	30
40	Classification of stacking faults and dislocations observed in nonpolar a-plane GaN epilayers using transmission electron microscopy. Applied Surface Science, 2012, 258, 2522-2528.	3.1	29
41	UVA light-emitting diode grown on Si substrate with enhanced electron and hole injections. Optics Letters, 2017, 42, 4533.	1.7	29
42	Room-temperature electrically pumped InGaIn-based microdisk laser grown on Si. Optics Express, 2018, 26, 5043.	1.7	29
43	Reverse leakage and breakdown mechanisms of vertical GaN-on-Si Schottky barrier diodes with and without implanted termination. Applied Physics Letters, 2021, 118, .	1.5	26
44	AlGaIn-based Schottky barrier deep ultraviolet photodetector grown on Si substrate. Optics Express, 2020, 28, 17188.	1.7	26
45	GaN-based ultraviolet microdisk laser diode grown on Si. Photonics Research, 2019, 7, B32.	3.4	25
46	Electrical properties and deep traps spectra of a-plane GaN films grown on r-plane sapphire. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2010, 166, 220-224.	1.7	24
47	Capture and emission mechanisms of defect states at interface between nitride semiconductor and gate oxides in GaN-based metal-oxide-semiconductor power transistors. Journal of Applied Physics, 2019, 126, .	1.1	24
48	Nitrogen-Implanted Guard Rings for 600-V Quasi-Vertical GaN-on-Si Schottky Barrier Diodes With a BFOM of 0.26 GW/cm ² . IEEE Transactions on Electron Devices, 2021, 68, 5682-5686.	1.6	24
49	High f_{T} AlGa(In)N/GaN HEMTs Grown on Si With a Low Gate Leakage and a High ON/OFF Current Ratio. IEEE Electron Device Letters, 2018, 39, 576-579.	2.2	23
50	Effect of Thermal Cleaning Prior to p-GaN Gate Regrowth for Normally Off High-Electron-Mobility Transistors. ACS Applied Materials & Interfaces, 2019, 11, 21982-21987.	4.0	22
51	Recovery of p-GaN surface damage induced by dry etching for the formation of p-type Ohmic contact. Applied Physics Express, 2019, 12, 055507.	1.1	22
52	Off-state electrical breakdown of AlGaIn/GaN/Ga(Al)N HEMT heterostructure grown on Si(111). AIP Advances, 2016, 6, .	0.6	21
53	High-power AlGaIn-based near-ultraviolet light-emitting diodes grown on Si(111). Applied Physics Express, 2017, 10, 072101.	1.1	21
54	Monolithic integration of E/D-mode GaN MIS-HEMTs on ultrathin-barrier AlGaIn/GaN heterostructure on Si substrates. Applied Physics Express, 2019, 12, 024001.	1.1	21

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55	Hydrogen sensing of N-polar and Ga-polar GaN Schottky diodes. Sensors and Actuators B: Chemical, 2009, 142, 175-178.	4.0	20
56	High efficient GaN-based laser diodes with tunnel junction. Applied Physics Letters, 2013, 103, 043508.	1.5	20
57	Growth evolution and microstructural characterization of semipolar (112̄,2) GaN selectively grown on etched r-plane sapphire. Journal of Crystal Growth, 2012, 341, 27-33.	0.7	19
58	Fabrication of normally-off AlGaIn/GaN metal-insulator-semiconductor high-electron-mobility transistors by photo-electrochemical gate recess etching in ionic liquid. Applied Physics Express, 2016, 9, 084102.	1.1	19
59	Wafer-scale crack-free 10 μm -thick GaN with a dislocation density of $5.8 \times 10^7 \text{ cm}^{-2}$ grown on Si. Journal Physics D: Applied Physics, 2019, 52, 425102.	1.5	19
60	Properties of AlN film grown on Si (111). Journal of Crystal Growth, 2016, 435, 76-83.	0.7	18
61	Determination of carbon-related trap energy level in (Al)GaIn buffers for high electron mobility transistors through a room-temperature approach. Applied Physics Letters, 2020, 117, .	1.5	18
62	Effect of NH ₃ flow rate on m-plane GaN growth on m-plane SiC by metalorganic chemical vapor deposition. Journal of Crystal Growth, 2009, 311, 3824-3829.	0.7	16
63	Surface and interface states of gallium-polar versus nitrogen-polar GaN: Impact of thin organic semiconductor overlayers. Journal of Applied Physics, 2010, 107, .	1.1	16
64	Continuous-wave electrically injected GaN-on-Si microdisk laser diodes. Optics Express, 2020, 28, 12201.	1.7	16
65	Spatial distribution of deep level defects in crack-free AlGaIn grown on GaN with a high-temperature AlN interlayer. Journal of Applied Physics, 2006, 100, 123101.	1.1	14
66	Effects of matrix layer composition on the structural and optical properties of self-organized InGaIn quantum dots. Journal of Applied Physics, 2013, 114, .	1.1	14
67	Investigation of InGaIn/GaN laser degradation based on luminescence properties. Journal of Applied Physics, 2016, 119, .	1.1	14
68	<i>a</i> -Axis GaIn/AlIn/AlGaIn Core-Shell Heterojunction Microwires as Normally Off High Electron Mobility Transistors. ACS Applied Materials & Interfaces, 2017, 9, 41435-41442.	4.0	14
69	Crack-free high quality 2 μm -thick Al _{0.5} Ga _{0.5} N grown on a Si substrate with a superlattice transition layer. CrystEngComm, 2020, 22, 1160-1165.	1.3	14
70	Influence of the carrier behaviors in p-GaN gate on the threshold voltage instability in the normally off high electron mobility transistor. Applied Physics Letters, 2021, 119, .	1.5	14
71	An Enhancement-Mode GaN p-FET With Improved Breakdown Voltage. IEEE Electron Device Letters, 2022, 43, 1191-1194.	2.2	14
72	UV LED arrays at 280 and 340 nm for spectroscopic biosensing. Physica Status Solidi (A) Applications and Materials Science, 2007, 204, 2112-2116.	0.8	13

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73	Stress evolution in AlN and GaN grown on Si(111): experiments and theoretical modeling. Journal of Materials Science: Materials in Electronics, 2016, 27, 2004-2013.	1.1	13
74	Effects of grain size on the mosaic tilt and twist in InN films grown on GaN by metal-organic chemical vapor deposition. Applied Physics Letters, 2006, 89, 092114.	1.5	12
75	Performance improvement of InGaN-based laser grown on Si by suppressing point defects. Optics Express, 2019, 27, 25943.	1.7	12
76	Study on the thermal stability of InN by in-situ laser reflectance system. Journal of Crystal Growth, 2005, 281, 310-317.	0.7	11
77	High-temperature AlN interlayer for crack-free AlGaIn growth on GaN. Journal of Applied Physics, 2008, 104, 043516.	1.1	11
78	Effect of gate orientation on dc characteristics of Si-doped, nonpolar AlGaIn/GaN metal-oxide semiconductor high electron mobility transistors. Applied Physics Letters, 2009, 95, 082110.	1.5	11
79	Surface striation, anisotropic in-plane strain, and degree of polarization in nonpolar m-plane GaN grown on SiC. Journal Physics D: Applied Physics, 2011, 44, 375103.	1.3	11
80	Optical emission characteristics of semipolar (1,1,ar{2},2) GaN light-emitting diodes grown on m-sapphire and stripe-etched<i>r</i>-sapphire. Semiconductor Science and Technology, 2012, 27, 024016.	1.0	11
81	Identification of Semi-ON-State Current Collapse in AlGaIn/GaN HEMTs by Drain Current Deep Level Transient Spectroscopy. IEEE Electron Device Letters, 2022, 43, 200-203.	2.2	11
82	Electrical and luminescent properties and deep traps spectra of N-polar GaN films. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2010, 166, 83-88.	1.7	10
83	Light output improvement of GaN-based light-emitting diodes grown on Si (111) by a via-thin-film structure. Journal of Semiconductors, 2018, 39, 044002.	2.0	10
84	InGaIn-Based Quantum Well Superluminescent Diode Monolithically Grown on Si. ACS Photonics, 2019, 6, 2104-2109.	3.2	10
85	A 30 Mbps in-plane full-duplex light communication using a monolithic GaN photonic circuit. Semiconductor Science and Technology, 2017, 32, 075002.	1.0	9
86	Accurate surface band bending determination on Ga-polar <i>n</i>-type GaN films by fitting x-ray valence band photoemission spectrum. AIP Advances, 2019, 9, .	0.6	9
87	GaN LEDs on Si Substrate. Solid State Lighting Technology and Application Series, 2019, , 133-170.	0.3	9
88	Thermal characterization of electrically injected GaN-based microdisk lasers on Si. Applied Physics Express, 2020, 13, 074002.	1.1	9
89	Interface Charge Effects on 2-D Electron Gas in Vertical-Scaled Ultrathin-Barrier AlGaIn/GaN Heterostructure. IEEE Transactions on Electron Devices, 2021, 68, 36-41.	1.6	9
90	Enhanced carrier confinement and radiative recombination in GaN-based lasers by tailoring first-barrier doping. Optics Express, 2020, 28, 32124.	1.7	9

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91	Evolution of mosaic structure in InN grown by metalorganic chemical vapor deposition. Journal of Crystal Growth, 2006, 293, 269-272.	0.7	8
92	Highly linearly polarized white light emission from InGaN light-emitting diode with nanograting-integrated fluorescent ceramics. Applied Physics Express, 2017, 10, 012101.	1.1	8
93	InGaN-Based Lasers with an Inverted Ridge Waveguide Heterogeneously Integrated on Si(100). ACS Photonics, 2020, 7, 2636-2642.	3.2	8
94	Gate Reliability and its Degradation Mechanism in the Normally OFF High-Electron-Mobility Transistors With Regrown p-GaN Gate. IEEE Journal of Emerging and Selected Topics in Power Electronics, 2021, 9, 3715-3724.	3.7	8
95	Heteroepitaxy of Nonpolar and Semipolar GaN. Springer Series in Materials Science, 2012, , 1-27.	0.4	8
96	Nitride-organic hybrid heterostructures for possible novel optoelectronic devices: charge injection and transport. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 593-595.	0.8	7
97	AlGaIn/GaN metal-insulator-semiconductor high electron mobility transistors with reduced leakage current and enhanced breakdown voltage using aluminum ion implantation. Applied Physics Letters, 2016, 108, .	1.5	7
98	Efficiency improvement of GaN-on-silicon thin-film light-emitting diodes with optimized via-like n-electrodes. Semiconductor Science and Technology, 2017, 32, 075009.	1.0	7
99	A Study of Efficiency Droop Phenomenon in GaN-Based Laser Diodes before Lasing. Materials, 2017, 10, 482.	1.3	7
100	Unintentional incorporation of Ga in the nominal AlN spacer of AlInGaIn/AlN/GaN Heterostructure. Journal Physics D: Applied Physics, 2018, 51, 035102.	1.3	7
101	Observation of oxide precipitates in InN nanostructures. Applied Physics Letters, 2007, 91, .	1.5	6
102	Thermal degradation of InGaIn/GaN quantum wells in blue laser diode structure during the epitaxial growth. Proceedings of SPIE, 2017, , .	0.8	6
103	Improving the Current Spreading by Locally Modulating the Doping Type in the n-AlGaIn Layer for AlGaIn-Based Deep Ultraviolet Light-Emitting Diodes. Nanoscale Research Letters, 2019, 14, 268.	3.1	6
104	Effect of surface stoichiometry on the non-alloyed ohmic contact to N-face n-GaN. Solid-State Electronics, 2020, 171, 107863.	0.8	6
105	A p-GaN-Gated Hybrid Anode Lateral Diode with a Thicker AlGaIn Barrier Layer. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900781.	0.8	6
106	An ultrathin-barrier AlGaIn/GaN heterostructure: a recess-free technology for the fabrication and integration of GaN-based power devices and power-driven circuits. Semiconductor Science and Technology, 2021, 36, 044002.	1.0	6
107	Effect of Si Doping on the Performance of GaN Schottky Barrier Ultraviolet Photodetector Grown on Si Substrate. Photonics, 2021, 8, 28.	0.9	6
108	Effects of Thickness of a Low-Temperature Buffer and Impurity Incorporation on the Characteristics of Nitrogen-polar GaN. Nanoscale Research Letters, 2016, 11, 509.	3.1	5

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109	Effects of thickness on optical characteristics and strain distribution of thin-film GaN light-emitting diodes transferred to Si substrates. <i>Applied Physics Express</i> , 2016, 9, 042101.	1.1	5
110	Catalytic growth of highly crystalline polyaniline by copper under ambient conditions. <i>CrystEngComm</i> , 2018, 20, 5119-5122.	1.3	5
111	Fabrication of AlGaIn nanostructures by nanolithography on ultraviolet LEDs grown on Si substrates. <i>Nanotechnology</i> , 2019, 30, 185201.	1.3	5
112	Evidence of a strong perpendicular magnetic anisotropy in Au/Co/MgO/GaN heterostructures. <i>Nanoscale Advances</i> , 2019, 1, 4466-4475.	2.2	5
113	Degradation study of InGaIn-based laser diodes grown on Si. <i>Journal Physics D: Applied Physics</i> , 2020, 53, 395103.	1.3	5
114	Electrically injected GaN-on-Si blue microdisk laser diodes. <i>Optics Express</i> , 2022, 30, 13039.	1.7	5
115	Improved minority carrier lifetime in p-type GaN by suppressing the non-radiative recombination process. <i>Applied Physics Express</i> , 2022, 15, 075501.	1.1	5
116	The Role of Growth-Pressure on the Determination of Anisotropy Properties in Nonpolar-m-Plane GaN. <i>ECS Journal of Solid State Science and Technology</i> , 2012, 1, R50-R53.	0.9	4
117	Preparation of GaN-on-Si based thin-film flip-chip LEDs. <i>Journal of Semiconductors</i> , 2013, 34, 053006.	2.0	4
118	Mechanism of leakage of ion-implantation isolated AlGaIn/GaN MIS-high electron mobility transistors on Si substrate. <i>Solid-State Electronics</i> , 2017, 134, 39-45.	0.8	4
119	Activation of buried p-GaN through nanopipes in large-size GaN-based tunnel junction LEDs. <i>Nanotechnology</i> , 2021, 32, 30LT01.	1.3	4
120	Suppression of unintentional carbon incorporation in AlGaIn-based near-ultraviolet light-emitting diode grown on Si. <i>Journal of Nanophotonics</i> , 2018, 12, 1.	0.4	4
121	Depth dependence of structural quality in InN grown by metalorganic chemical vapor deposition. <i>Materials Letters</i> , 2007, 61, 516-519.	1.3	3
122	Nonpolar and semipolar GaN heteroepitaxy on sapphire for LED application. , 2010, , .		3
123	Revealing the Positive Bias Temperature Instability in Normally-OFF AlGaIn/GaN MIS-HFETs by Constant-Capacitance DLTS. , 2019, , .		3
124	Self-terminated Gate Recessing with a Low Density of Interface States and High Uniformity for Enhancement-mode GaN HEMTs. , 2020, , .		3
125	Influence of traps on the gate reverse characteristics of normally-off high-electron-mobility transistors with regrown p-GaN gate. <i>Applied Physics Express</i> , 2021, 14, 104005.	1.1	3
126	GaN-Based Resonant-Cavity Light-Emitting Diodes Grown on Si. <i>Nanomaterials</i> , 2022, 12, 134.	1.9	3

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127	Influence of Mg doping level at the initial growth stage on the gate reliability of p-GaN gate HEMTs. Journal Physics D: Applied Physics, 2022, 55, 355103.	1.3	3
128	The abnormal aging phenomena in GaN-based near-ultraviolet laser diodes. Journal Physics D: Applied Physics, 2019, 52, 275104.	1.3	2
129	Narrow-Linewidth GaN-on-Si Laser Diode with Slot Gratings. Nanomaterials, 2021, 11, 3092.	1.9	2
130	GaN-based distributed feedback laser diodes grown on Si. Journal Physics D: Applied Physics, 2022, 55, 195103.	1.3	2
131	Influence of cracks generation on the structural and optical properties of GaN/Al _{0.55} Ga _{0.45} N multiple quantum wells. Applied Surface Science, 2006, 252, 3043-3050.	3.1	1
132	a-plane GaN hydride vapor phase epitaxy on a-plane GaN templates with and without use of TiN intermediate layers. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2010, 28, 1039-1043.	0.6	1
133	Growth of cubic InN on GaP(110) with GaN buffer by metalorganic chemical vapour deposition. Journal Physics D: Applied Physics, 2011, 44, 285403.	1.3	1
134	A fixed cytometer chip for identification of cell populations and real-time monitoring of single-cell apoptosis under gradient UV radiation. Microfluidics and Nanofluidics, 2019, 23, 1.	1.0	1
135	Structure and luminescence of a-plane GaN on r-plane sapphire substrate modified by Si implantation*. Chinese Physics B, 2021, 30, 056104.	0.7	1
136	Nitride/organic hybrid heterostructures for photodetector devices. , 2008, , .		0
137	High Sensitivity of Hydrogen Sensing Through N-polar GaN Schottky Diodes. Materials Research Society Symposia Proceedings, 2009, 1202, 178.	0.1	0
138	Optical Characterization of Semipolar GaN Light-Emitting Diodes on Sapphire. , 2011, , .		0
139	Performance Enhancement of GaN-Based Laser Diodes With Prestrained Growth. IEEE Photonics Technology Letters, 2013, 25, 2401-2404.	1.3	0
140	Cost-effective solid state lighting based on GaN-on-Si technology. , 2013, , .		0
141	Effect of plasma surface treatment on embedded n-contact for GaN-based blue light-emitting diodes grown on Si substrate. Wuli Xuebao/Acta Physica Sinica, 2017, 66, 047801.	0.2	0